DESCRIPTION

mounting (SMD).

Vishay Semiconductors



High Speed Infrared Emitting Diode, RoHS Compliant, 850 nm, GaAlAs Double Hetero



VSMG3700 is an infrared, 850 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and

high speed, molded in a PLCC-2 package for surface

FEATURES

· Package type: surface mount

• Package form: PLCC-2

Dimensions (L x W x H in mm): 3.5 x 2.8 x 1.75

• Peak wavelength: $\lambda_p = 850 \text{ nm}$

· High reliability

High radiant power

· High radiant intensity

• Angle of half intensity: $\varphi = \pm 60^{\circ}$

· Low forward voltage

• Suitable for high pulse current operation

• High modulation band width: f_c = 18 MHz

· Good spectral matching with Si photodetectors

• Floor life: 4 weeks, MSL 2a, acc. J-STD-020

· Lead (Pb)-free reflow soldering

 Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC

APPLICATIONS

- Infrared radiation source for operation with CMOS cameras (illumination)
- High speed IR data transmission

| PRODUCT SUMMARY | | | | | |
|-----------------|------------------------|---------|---------------------|---------------------|--|
| COMPONENT | I _e (mW/sr) | φ (deg) | λ _P (nm) | t _r (ns) | |
| VSMG3700 | 10 | ± 60 | 850 | 20 | |

Note

Test conditions see table "Basic Characteristics"

| ORDERING INFORMATION | | | | | |
|----------------------|---------------|------------------------------|--------------|--|--|
| ORDERING CODE | PACKAGING | REMARKS | PACKAGE FORM | | |
| VSMG3700-GS08 | Tape and reel | MOQ: 7500 pcs, 1500 pcs/reel | PLCC-2 | | |
| VSMG3700-GS18 | Tape and reel | MOQ: 8000 pcs, 8000 pcs/reel | PLCC-2 | | |

Note

MOQ: minimum order quantity

| ABSOLUTE MAXIMUM RATINGS | | | | |
|--------------------------|--------------------------------|------------------|-------|------|
| PARAMETER | TEST CONDITION | SYMBOL | VALUE | UNIT |
| Reverse voltage | | V_{R} | 5 | V |
| Forward current | | I _F | 100 | mA |
| Peak forward current | $t_p/T = 0.5, t_p = 100 \mu s$ | I _{FM} | 200 | mA |
| Surge forward current | t _p = 100 μs | I _{FSM} | 1 | Α |
| Power dissipation | | P _V | 180 | mW |







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| ABSOLUTE MAXIMUM RATINGS | | | | |
|-------------------------------------|----------------------------|------------------|---------------|------|
| PARAMETER | TEST CONDITION | SYMBOL | VALUE | UNIT |
| Junction temperature | | T _j | 100 | °C |
| Operating temperature range | | T _{amb} | - 40 to + 85 | °C |
| Storage temperature range | | T _{stg} | - 40 to + 100 | °C |
| Soldering temperature | acc. figure 8, J-STD-020 | T _{sd} | 260 | °C |
| Thermal resistance junction/ambient | J-STD-051, soldered on PCB | R_{thJA} | 250 | K/W |

Note

 T_{amb} = 25 °C, unless otherwise specified

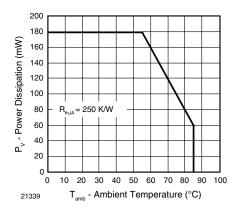


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

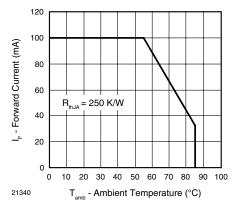


Fig. 2 - Forward Current Limit vs. Ambient Temperature

| BASIC CHARACTERISTICS | | | | | | |
|---|---|------------------|------|--------|------|-------|
| PARAMETER | TEST CONDITION | SYMBOL | MIN. | TYP. | MAX. | UNIT |
| Forward voltage | I _F = 100 mA, t _p = 20 ms | V _F | | 1.5 | 1.8 | V |
| Forward voltage | $I_F = 1 \text{ A}, t_p = 100 \ \mu\text{s}$ | V _F | | 2.3 | | V |
| Temperature coefficient of V _F | I _F = 1 mA | TK _{VF} | | - 1.8 | | mV/K |
| Reverse current | V _R = 5 V | I _R | | | 10 | μΑ |
| Junction capacitance | V _R = 0 V, f = 1 MHz, E = 0 | C _j | | 125 | | pF |
| Dedient intensity | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$ | I _e | 6 | 10 | 22 | mW/sr |
| Radiant intensity | $I_F = 1 \text{ A}, t_p = 100 \ \mu\text{s}$ | l _e | | 100 | | mW/sr |
| Radiant power | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$ | φe | | 40 | | mW |
| Temperature coefficient of ϕ_e | I _F = 100 mA | TKφ _e | | - 0.35 | | %/K |
| Angle of half intensity | | φ | | ± 60 | | deg |
| Peak wavelength | I _F = 100 mA | λ_{p} | | 850 | | nm |
| Spectral bandwidth | I _F = 100 mA | Δλ | | 40 | | nm |
| Temperature coefficient of λ_p | I _F = 100 mA | TKλ _p | | 0.25 | | nm/K |
| Rise time | I _F = 100 mA | t _r | | 20 | | ns |
| Fall time | I _F = 100 mA | t _f | | 13 | | ns |
| Cut-off frequency | I _{DC} = 70 mA, I _{AC} = 30 mA pp | f _c | | 18 | | MHz |
| Virtual source diameter | | d | | 0.44 | | mm |

Note

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BASIC CHARACTERISTICS

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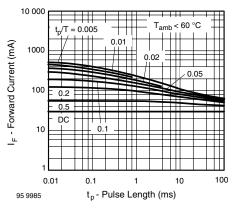


Fig. 3 - Pulse Forward Current vs. Pulse Duration

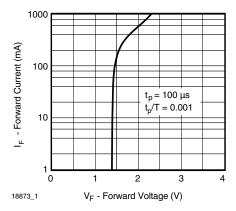


Fig. 4 - Forward Current vs. Forward Voltage

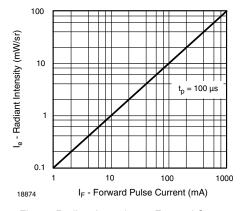


Fig. 5 - Radiant Intensity vs. Forward Current

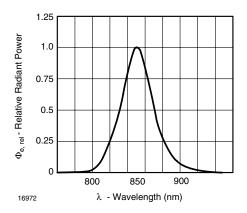


Fig. 6 - Relative Radiant Power vs. Wavelength

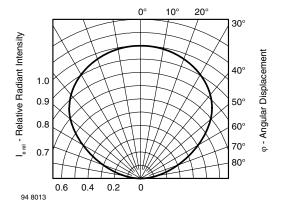


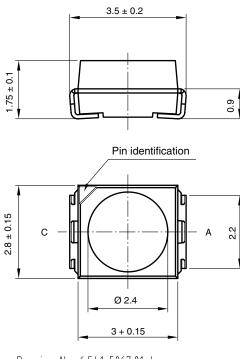
Fig. 7 - Relative Radiant Intensity vs. Angular Displacement



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PACKAGE DIMENSIONS in millimeters



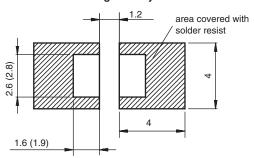
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Mounting Pad Layout



SOLDER PROFILE

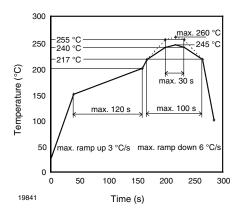


Fig. 8 - Lead (Pb)-free Reflow Solder Profile acc. J-STD-020D

DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

FLOOR LIFE

Floor life (time between soldering and removing from MBB) must not exceed the time indicated on MBB label:

Floor life: 4 weeks

Conditions: T_{amb} < 30 °C, RH < 60 %

Moisture sensitivity level 2a, acc. to J-STD-020.

DRYING

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or label. Devices taped on reel dry using recommended conditions 192 h at 40 $^{\circ}$ C (+ 5 $^{\circ}$ C), RH < 5 $^{\circ}$ M.

TAPE AND REEL

PLCC-2 components are packed in antistatic blister tape (DIN IEC (CO) 564) for automatic component insertion. Cavities of blister tape are covered with adhesive tape.

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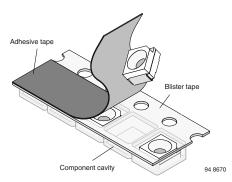


Fig. 9 - Blister Tape

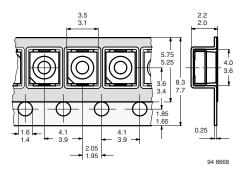


Fig. 10 - Tape Dimensions in mm for PLCC-2

MISSING DEVICES

A maximum of 0.5 % of the total number of components per reel may be missing, exclusively missing components at the beginning and at the end of the reel. A maximum of three consecutive components may be missing, provided this gap is followed by six consecutive components.

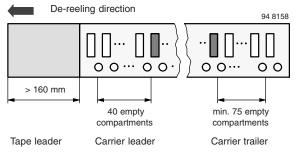


Fig. 11 - Beginning and End of Reel

The tape leader is at least 160 mm and is followed by a carrier tape leader with at least 40 empty compartments. The tape leader may include the carrier tape as long as the cover tape is not connected to the carrier tape. The least component is followed by a carrier tape trailer with a least 75 empty compartments and sealed with cover tape.

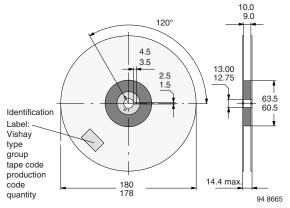


Fig. 12 - Dimensions of Reel-GS08

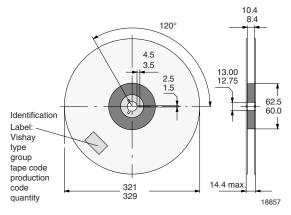


Fig. 13 - Dimensions of Reel-GS18

COVER TAPE REMOVAL FORCE

The removal force lies between 0.1 N and 1.0 N at a removal speed of 5 mm/s. In order to prevent components from popping out of the blisters, the cover tape must be pulled off at an angle of 180° with regard to the feed direction.



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